

TOSHIBA**2SC2883**

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2883

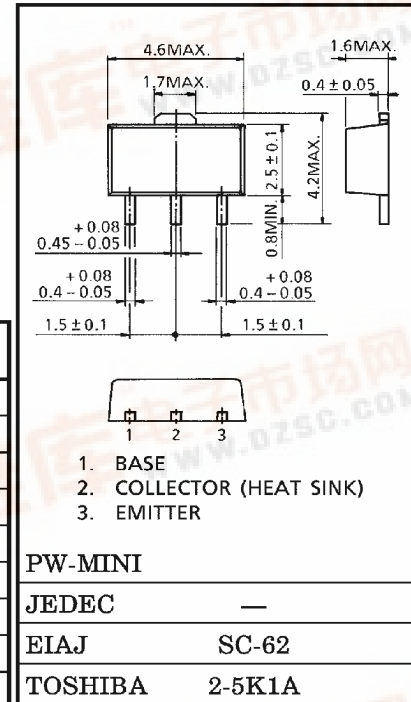
AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

Unit in mm

- Suitable for Output Stage of 3 Watts Amplifier
- $P_C=1\sim 2W$ (Mounted Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1203

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	30	V
Collector-Emitter Voltage	V_{CE0}	30	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	1.5	A
Base Current	I_B	0.3	A
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C (Note)	1000	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ C$

Note : Mounted on ceramic substrate ($250mm^2\times 0.8t$)Weight : 0.05g
Marking

Type Name

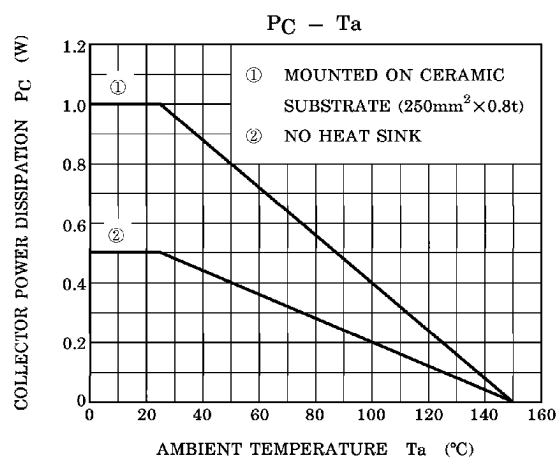
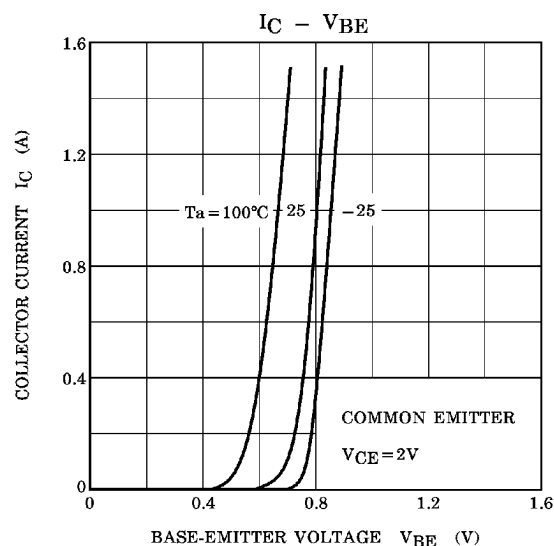
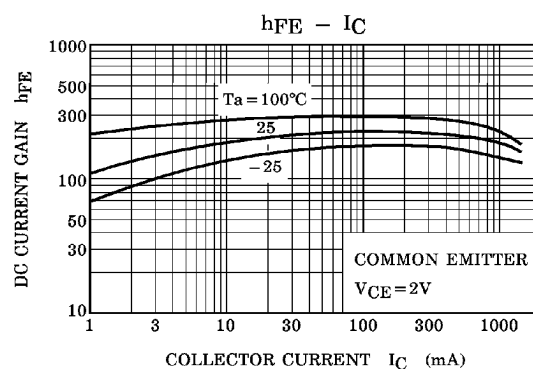
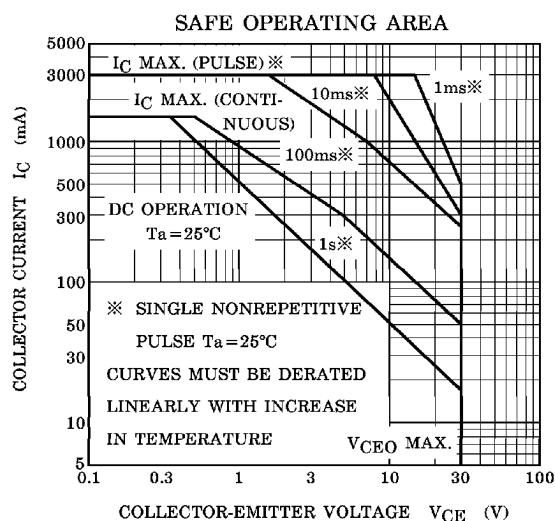
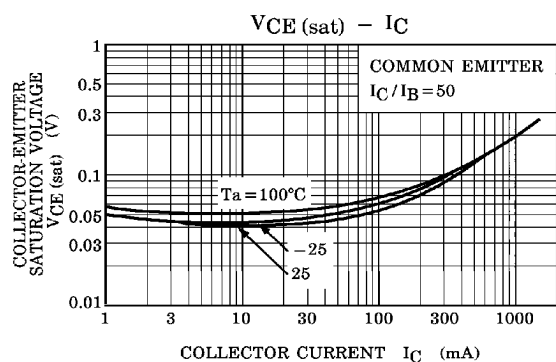
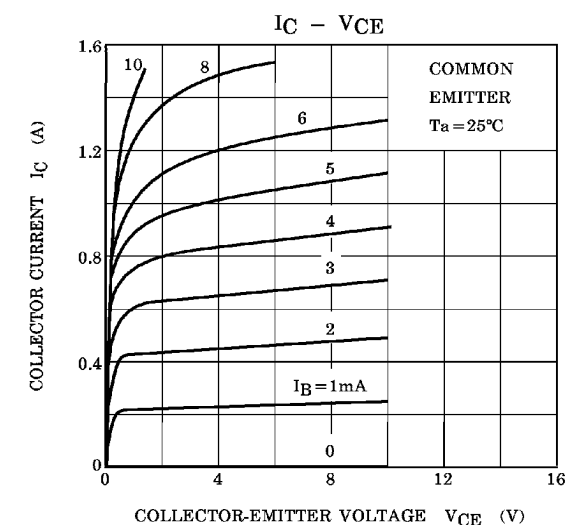
 h_{FE} RankELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB}=30V, I_E=0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=5V, I_C=0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CE0}$	$I_C=10mA, I_B=0$	30	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EB0}$	$I_E=1mA, I_C=0$	5	—	—	V
DC Current Gain	h_{FE} (Note)	$V_{CE}=2V, I_C=500mA$	100	—	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=0.03A$	—	—	2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=2V, I_C=500mA$	—	—	1.0	V
Transition Frequency	f_T	$V_{CE}=2V, I_C=500mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	—	—	40	pF

Note : h_{FE} Classification O : 100~200, Y : 160~320

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